CGD1040HI

1 GHz, 20 dB gain GaAs high output power doubler Rev. 01 — 22 September 2009 Produc

Product data sheet

Product profile

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

1.2 Features

- Excellent linearity
- Superior levels of ESD protection
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Compliant to Directive 2002/95/EC, regarding Restriction of the use of certain Hazardous Substances (RoHS)
- Integrated ring wave surge protection

1.3 Applications

■ CATV systems operating in the 40 MHz to 1003 MHz frequency range

1.4 Quick reference data

Quick reference data

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 ^{\circ}\text{C}$; unless otherwise specified.

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------|----------------------------|---------------------------------------|-----|------|------|------|------|
| Gp | power gain | f = 50 MHz | | - | 20 | - | dB |
| | | f = 1003 MHz | | 19.5 | 20.8 | 22.0 | dB |
| СТВ | composite triple beat | $V_0 = 56.4 \text{ dBmV}$ at 1003 MHz | [1] | - | -74 | -64 | dBc |
| CCN | carrier-to-composite noise | $V_0 = 56.4 \text{ dBmV}$ at 1003 MHz | [1] | 57 | 63 | - | dBc |
| I _{tot} | total current | | [2] | - | 440 | 460 | mΑ |

^{[1] 79} NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.



^[2] Direct Current (DC).

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2. Pinning information

Table 2. Pinning

| | 9 | |
|------|-----------------|-----------------------------------|
| Pin | Description | Simplified outline Graphic symbol |
| 1 | input | |
| 2, 3 | common | 1 3 5 7 9 |
| 5 | +V _B | |
| 7, 8 | common | 12 3 7 8 |
| 9 | output | sym095 |
| | | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| CGD1040HI | - | rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 × 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads | SOT115J | | |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------------|---|-----|-----|------|------|
| V_{B} | supply voltage | | | - | 30 | V |
| $V_{i(RF)}$ | RF input voltage | single tone | | - | 75 | dBmV |
| V _{ESD} | electrostatic discharge voltage | Human Body Model (HBM); According JEDEC standard 22-A114E | [1] | - | 2000 | V |
| | | Biased; According IEC61000-4-2 | | - | 1500 | V |
| T _{stg} | storage temperature | | | -40 | +100 | °C |
| T _{mb} | mounting base temperature | | | -20 | +100 | °C |

^[1] The ESD pulse of 2000 V corresponds to a class 2 sensitivity level.

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5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24~V~(DC)$; $Z_S = Z_L = 75~\Omega$; $T_{mb} = 35~^{\circ}C$; unless otherwise specified.

| | | 7 | | • | | | |
|------------------|-----------------------------------|--|------------|------|------|------|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| G_p | power gain | f = 50 MHz | | - | 20 | - | dB |
| | | f = 1003 MHz | | 19.5 | 20.8 | 22.0 | dB |
| SL _{sl} | slope straight line | f = 40 MHz to 1003 MHz | <u>[1]</u> | 0.5 | - | 2 | dB |
| FL | flatness of frequency response | f = 40 MHz to 1003 MHz | [2] | - | - | 1 | dB |
| RL_{in} | input return loss | f = 40 MHz to 160 MHz | | 20 | - | - | dB |
| | | f = 160 MHz to 320 MHz | | 20 | - | - | dB |
| | | f = 320 MHz to 640 MHz | | 18 | - | - | dB |
| | | f = 640 MHz to 870 MHz | | 16 | - | - | dB |
| | | f = 870 MHz to 1003 MHz | | 16 | - | - | dB |
| RL_{out} | output return loss | f = 40 MHz to 160 MHz | | 20 | - | - | dB |
| | | f = 160 MHz to 320 MHz | | 20 | - | - | dB |
| | | f = 320 MHz to 640 MHz | | 18 | - | - | dB |
| | | f = 640 MHz to 870 MHz | | 16 | - | - | dB |
| | | f = 870 MHz to 1003 MHz | | 16 | - | - | dB |
| NF | noise figure | f = 50 MHz | | - | 5 | 6 | dB |
| | | f = 1003 MHz | | - | 5.5 | 6.5 | dB |
| I _{tot} | total current | | [3] | - | 440 | 460 | mA |
| 79 NTSC | channels + 75 digital channels | | | | | | |
| СТВ | composite triple beat | V _o = 56.4 dBmV at 1003 MHz | <u>[4]</u> | - | -74 | -64 | dBc |
| CSO | composite second-order distortion | V _o = 56.4 dBmV at 1003 MHz | <u>[4]</u> | - | -78 | -65 | dBc |
| Xmod | cross modulation | V _o = 56.4 dBmV at 1003 MHz | <u>[4]</u> | - | -68 | - | dB |
| CCN | carrier-to-composite noise | $V_0 = 56.4 \text{ dBmV}$ at 1003 MHz | <u>[4]</u> | 57 | 63 | - | dBc |
| 79 NTSC | channels | | | | | | |
| СТВ | composite triple beat | V _o = 58.4 dBmV at 1003 MHz | [5] | - | -70 | - | dBc |
| CSO | composite second-order distortion | V _o = 58.4 dBmV at 1003 MHz | [5] | - | -76 | - | dBc |
| Xmod | cross modulation | V _o = 58.4 dBmV at 1003 MHz | [5] | - | -66 | - | dB |
| | | | | | | | |

^[1] G_p at 1003 MHz minus G_p at 40 MHz.

^[2] Flatness is defined as peak deviation to straight line.

^[3] Direct Current (DC).

^{[4] 79} NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

^{[5] 79} NTSC channels [f = 54 MHz to 550 MHz]; tilt extrapolated to 13.5 dB at 1003 MHz.

6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

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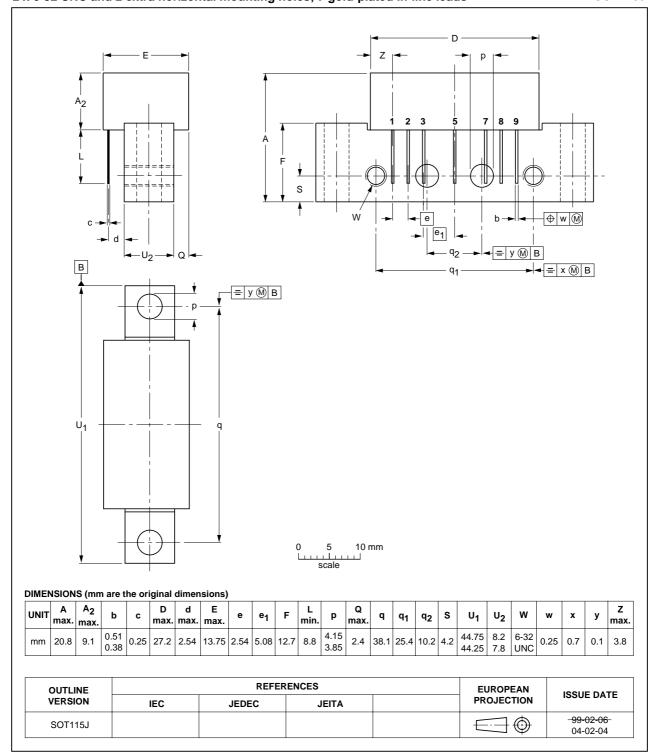


Fig 1. Package outline SOT115J

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7. Abbreviations

Table 6. Abbreviations

| Acronym | Description |
|---------|--|
| CATV | Community Antenna TeleVision |
| ESD | ElectroStatic Discharge |
| GaAs | Gallium-Arsenide |
| NTSC | National Television Standard Committee |
| RF | Radio Frequency |
| UNC | UNified Coarse |

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| CGD1040HI_1 | 20090922 | Product data sheet | - | - |

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9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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